



2812

PATENT**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

MANFRED HORSTMANN
ROLF STEPHAN
KARSTEN WIECZOREK
STEPHEN KRUEGEL

Examiner: Unknown

Group Art Unit: 2812

Serial No.: 09/847,622

Att'y Docket: 2000.064200/DE0053

Filed: May 2, 2001

For: FIELD EFFECT TRANSISTOR WITH
REDUCED GATE DELAY AND
METHOD OF FABRICATING THE
SAME

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

CERTIFICATE OF MAILING 37 C.F.R. 1.8	
I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date below:	
October 1, 2001 Date	 Signature

Please amend the above-referenced patent application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A transistor, comprising:

a substrate;

an active region defined in said substrate;

a gate insulation layer formed above said active region; and

a gate electrode formed above said gate insulation layer, said gate electrode having a middle portion located over the active region, said middle portion having a gate

RECEIVED
OCT -9 2001
TC 2800 MAIL ROOM